

Notice of References Cited	Application/Control No. 10/056,179		Applicant(s)/Patent Under Reexamination TAYLOR, THEODORE M.	
	Examiner Howard Weiss		Art Unit 2814	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6,271,561	08-2001	Doan	257/316
	C	US-6,214,667	04-2001	Ding et al.	438/257
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	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

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	V	Shirai, H., et al., "A0.54 μm sq. Self-Aligned HSG Floating Gate Cell (SAHF Cell) for 256Mbit Falsh Memories", Dec. 1995, IEDM 95, pp. 653-6
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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